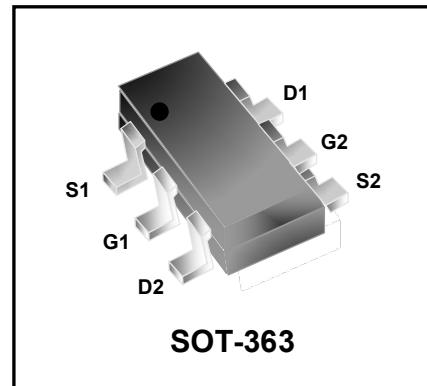


Features

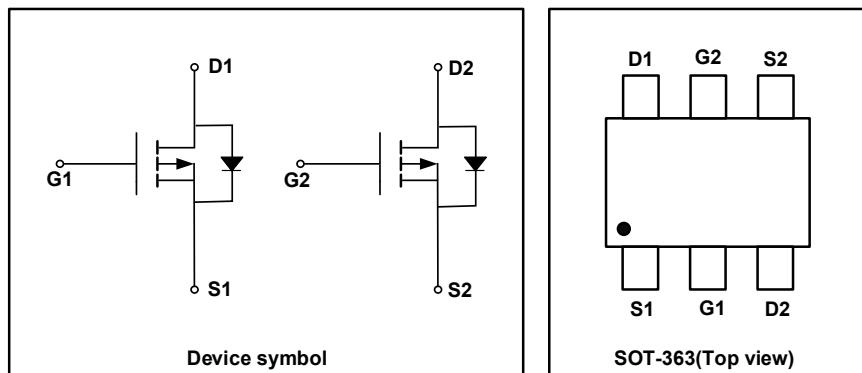
- Way-on Small Single MOSFETs
 - $V_{DS} = -50V$, $I_D = -0.13A$
 - $R_{DS(on)} < 6\Omega$ @ $V_{GS} = -10V$
 - $R_{DS(on)} < 7\Omega$ @ $V_{GS} = -5V$
 - Trench LV MOSFET Technology

Mechanical Characteristics

- SOT-363 Package
 - Marking : Making Code
 - RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-0.13	A
Pulsed Drain Current ¹	I_{DM}	-0.52	A
Power Dissipation	P_D	200	mW
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	R _{θJA}	625	°C/W

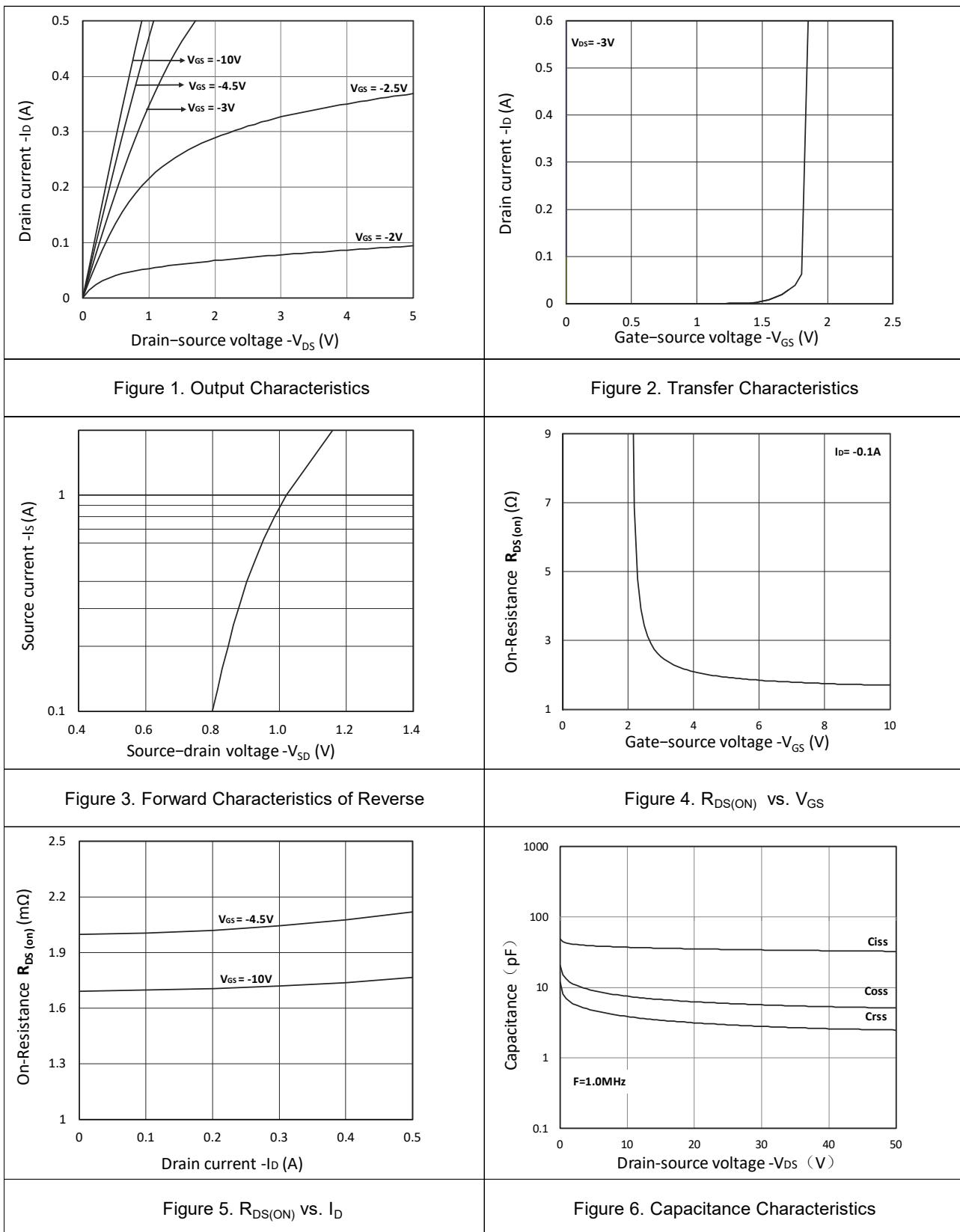
Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-50	-	-	V
Gate leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±1	μA
Drain Cut-off Current	I _{DSS}	V _{DS} = -50V, V _{GS} = 0V	-	-	-1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.8	-1.5	-2.1	V
Drain-Source On-state Resistance ³	R _{DS(on)}	V _{GS} = -10V, I _D = -0.1A	-	1.7	6	Ω
		V _{GS} = -4.5V, I _D = -0.1A	-	2	7	Ω
Dynamic characteristics⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -25V, f = 1MHz	-	35	-	pF
Output Capacitance	C _{oss}		-	6	-	
Reverse Transfer Capacitance	C _{rss}		-	3	-	
Switching Characteristics⁴						
Turn-on Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DD} = -25V, I _D = -0.1A, R _G = 3Ω	-	2.5	-	ns
Turn-on Rise Time	t _r		-	1	-	
Turn-off Delay Time	t _{d(off)}		-	16	-	
Turn-off Fall Time	t _f		-	8	-	
Source-Drain Diode characteristics						
Diode Forward Voltage ³	V _{SD}	I _S = -0.1A ,V _{GS} =0V,	-	-	-1.2	V
Continuous Source Current	I _S		-	-	-0.13	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

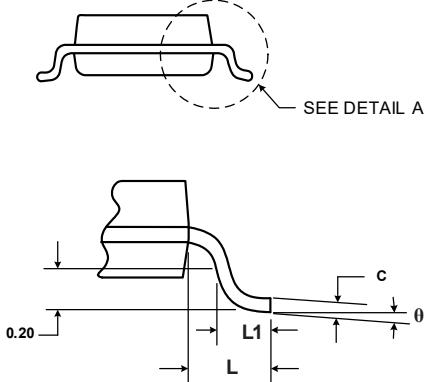


Outline Drawing – SOT-363

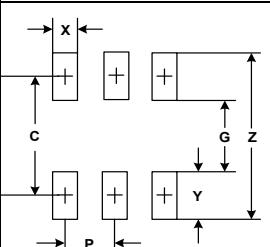
PACKAGE OUTLINE		SOT-363			
SYMBOL	DIMMETER		INCHES		
	MIN	MAX	MIN	MAX	
A	0.90	1.10	0.035	0.043	
A1	0.00	0.10	0.000	0.004	
b	0.15	0.35	0.006	0.014	
c	0.10	0.15	0.004	0.006	
D	2.00	2.20	0.079	0.087	
E1	1.15	1.35	0.045	0.053	
E	2.15	2.45	0.085	0.096	
e	0.650 TYP		0.026 TYP		
e1	1.20	1.40	0.047	0.055	
L	0.525 REF.		0.021 REF.		
L1	0.26	0.46	0.010	0.018	
θ	0°	8°	0°	8°	



SEE DETAIL A



DETAIL A

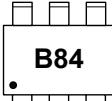


DIMENSIONS		
DIM	INCHES	MILLIMETERS
Z	0.110	2.79
G	0.043	1.09
C	0.076	1.94
P	0.026 TYP	0.65 TYP
X	0.016	0.40
Y	0.033	0.85

Notes

- Dimensioning and tolerances per ANSI Y14.5M, 1985.
- Controlling Dimension: Inches
- Pin 3 is the cathode (Unidirectional Only).
- Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM05DP01D
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.